

Yelong Xu, Mingyang Lyu, Leslie Rusch and Wei Shi* Centre d'optique, photonique et laser (COPL), Université Laval, Québec G1V 0A6, Canada. wei.shi@gel.ulaval.ca

ABSTRACT

We experimentally demonstrate SSB-OFDM signal generation with over 18-dB sideband suppression ratio using a silicon microring IQ modulator. Transmission of 31.4 Gb/s over 20km SSMF is achieved well below the FEC threshold.

INTRODUCTION

- OFDM for next generation PON:
 - Single sideband
 - Avoid frequency selective fading
 - Power conservation
 - Bandwidth conservation
 - Direct detection
 - Low cost and low complexity
- Current single sideband direct detection solution on silicon photonics chip:
 - Dual-drive MZM (DD-MZM)
 - Large device size and high power consumption
 - In-phase and quadrature Mach-Zehnder modulator (IQ-MZM) Complex driving scheme (four driving signals)

MRM MODULATOR BASED OPTICAL SSB TRANSMITTER



- CMOS-compatible and cheap (SiP solution)
- Compact device size (20um radius MRM)
- Power efficient (milliwatts level)
- Simple driving scheme (two driving signals)

Silicon Microring IQ Modulator Enabled Single Sideband OFDM Transmission

EXPERIMENT SET-UP



EXPERIMENTAL RESULT



Optical Spectrum for generated SSB-OFDM signal

CONCLUSION

- 18 dB side-band suppression ratio
- Robustness against chromatic dispersion
- Provides a low-cost integrated solution for SSB signal transmitter and has a great potential for WDM-PON applications.

ACKNOWLEDGEMENT

Quebec grant (52_Rusch 2016.09), TELUS and Aeponyx.

REFERENCE

- 1178-1180.
- Quantum Electronics 22.6 (2016): 370-378.
- (2018): 145-148.

-1 V -2 V -3 V -4 V - -5 V $\Delta f = 12.5 \text{ GHz}$ 15 Frequency (GHz)

(a) Partial mask layout for MRM1/MRM2, (b) cross section of the p-n junction of MRM1/ MRM2 showing relevant dimensions, for MRM1 measured (c) power transmission spectra at different bias voltages, and (d) electro-optic frequency response (S21) at different frequency detunings.



- 8-bit DAC with 16 GHz bandwidth running at 84 GSa/s
- Driving signals are amplified to 5V_{pp} by two 50 GHz RF amplifiers, and are sent to the chip via a GSGSG configured, 50 Ω RF probe
- RTO captures the signal at 80 Gsa/s with 30 GHz bandwidth



(a) Estimated SNR per subcarrier for DSB and SSB signals. (b) Constellations of received DSB and SSB signals. (c) BER of detected SSB OFDM signal with varied received power.

We demonstrate the 20 km SMF transmission of wide-band optical SSB OFDM (15.7-GHz bandwidth with a 2.7 GHz guard band) using an integrated silicon microring IQ modulator.



We thank CMC Microsystems for the multi-project wafer service. This work is supported by Fonds de Recherche du Québec-Nature et Technologies (FRQNT) (2016-NC-190737), National Science and Engineering Research Council of Canada (NSERC) (CRDPJ499664), PROMPT

[1] Dong, Po, et al. "Experimental demonstration of microring quadrature phase-shift keying modulators." Optics letters 37.7 (2012):

[2] Ruan, Xiaoke, et al. "Experimental comparison of direct detection Nyquist SSB transmission based on silicon dual-drive and IQ Mach-Zehnder modulators with electrical packaging." Optics express 25.16 (2017): 19332-19342.

[3] Dong, Po. "Silicon photonic integrated circuits for wavelength-division multiplexing applications." IEEE Journal of Selected Topics in

[4] Lyu, Mingyang, et al. "Single-Sideband OFDM Transmission via a Silicon Microring IQ Modulator." IEEE Photonics Technology Letters 31.2